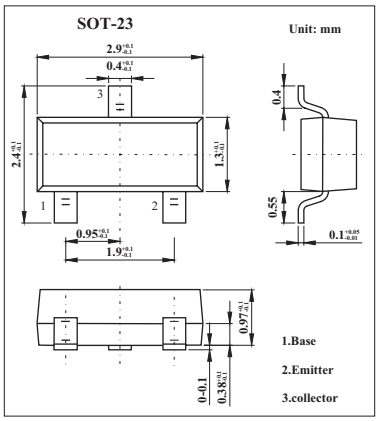
Silicon NPN Epitaxial

2SC3123



Features

- High Conversion Gain :Gce=23dB(TYP.)
- Low Reverse Transfer Capacitance : Cre=0.4F(TYP.)

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Base current	I_B	25	mA
Collector Power Dissipation	P_C	150	mW
Junction temperature	T_j	125	℃
Storage temperature Range	T_{stg}	-55 to +125	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 25V, I_E = 0			100	nA
Emitter cut-off current	I_{EBO}	V_{EB} = 3V, I_C = 0			1000	nA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	20			V
DC current gain	h_{FE}	V_{CE} = 10 V, I_C = 5mA	40	150	300	
Reverse Transfer Capacitance	C_{re}	V_{CB}=10V,I_E=0,f=1MHz		0.4	0.5	pF
Transition Frequency	f_T	V_{CE} = 10 V, I_C = 5mA	900	1400		MHz
Conversion Gain	G_{ce}	V_{CC}=12V,fL=260MHz,f=200MHZ	20	23		dB
Noise Figure	NF			3.8	5.5	dB

Marking

Marking	HE